

A cross-sectional view of a semiconductor device. It shows a substrate 12 with a layer 16 on top. A trench 18 is formed in layer 16, with a bottom surface 20. A layer 22 is deposited on the top surface and the side walls of the trench 18. An arrow 10 points to the trench 18.

A cross-sectional view of a semiconductor device. A substrate 12 is shown at the bottom. A layer 16 is formed on the substrate. A trench 10 is formed in the layer 16. A layer 20 is formed in the trench 10. A layer 22 is formed on the layer 16. A layer 24 is formed on the layer 22. A layer 26 is formed on the layer 24.

FIG. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 12, a layer 16, a layer 20, and a layer 22. A trench 24 is formed in the substrate, and a gate 28 is formed in the trench. An arrow 10 points to the gate 28.

6. Gold plating 14
(PRIOR ART)
FIG. 1F

FIG. 1G

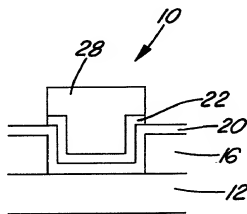


FIG. 1H

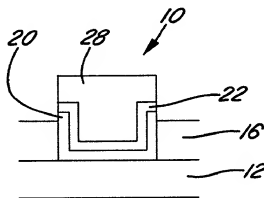


FIG. 11

